



Monolithic N-Channel JFET Dual

PRODUCT SUMMARY				
$V_{GS(off)}$ (V)	$V_{(BR)GSS}$ Min (V)	g_{fs} Min (mS)	I_G Max (pA)	$ V_{GS1} - V_{GS2} $ Max (mV)
-1.0 to -4.5	-50	1	-50	25

FEATURES

- Monolithic Design
- High Slew Rate
- Low Offset/Drift Voltage
- Low Gate Leakage: 5 pA
- Low Noise: 9 nV/√Hz
- High CMRR: 100 dB

BENEFITS

- Tight Differential Match vs. Current
- Improved Op Amp Speed, Settling Time Accuracy
- Minimum Input Error/Trimming Requirement
- Insignificant Signal Loss/Error Voltage
- High System Sensitivity
- Minimum Error with Large Input Signal

APPLICATIONS

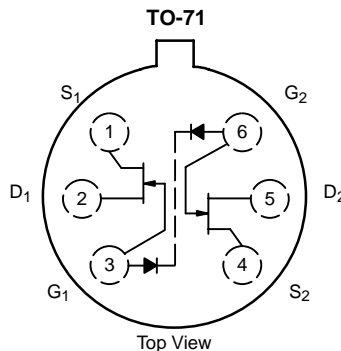
- Wideband Differential Amps
- High-Speed, Temp-Compensated, Single-Ended Input Amps
- High Speed Comparators
- Impedance Converters

DESCRIPTION

The low cost 2N3958 JFET dual is designed for high-performance differential amplification for a wide range of precision test instrumentation applications. This series features tightly matched specs, low gate leakage for accuracy, and wide dynamic range with I_G guaranteed at $V_{DG} = 20$ V.

The hermetically-sealed TO-71 package is available with full military processing (see Military Information and the 2N5545/5546/5547JANTX/JANTXV data sheet).

For similar products see 2N5196/5197/5198/5199, the low-noise U/SST401 series, the high-gain 2N5911/5912, and the low-leakage U421/423 data sheets.



ABSOLUTE MAXIMUM RATINGS

Gate-Drain, Gate-Source Voltage	-50 V
Gate Current	50 mA
Lead Temperature (1/16" from case for 10 sec.)	300 °C
Storage Temperature	-65 to 200 °C
Operating Junction Temperature	-55 to 150 °C

Power Dissipation :	Per Side ^a	250 mW
	Total ^b	500 mW

- Notes
- a. Derate 2 mW/°C above 85°C
 - b. Derate 4 mW/°C above 85°C

SPECIFICATIONS (T _A = 25 °C UNLESS OTHERWISE NOTED)						
Parameter	Symbol	Test Conditions	Limits			Unit
			Min	Typ ^a	Max	
Static						
Gate-Source Breakdown Voltage	V _{(BR)GSS}	I _G = -1 μA, V _{DS} = 0 V	-50	-57		V
Gate-Source Cutoff Voltage	V _{GS(off)}	V _{DS} = 20 V, I _D = 1 nA	-1.0	-2	-4.5	
Saturation Drain Current ^b	I _{DSS}	V _{DS} = 20 V, V _{GS} = 0 V	0.5	3	5	mA
Gate Reverse Current	I _{GSS}	V _{GS} = -30 V, V _{DS} = 0 V		-10	-100	pA
		T _A = 150 °C		-20	-500	nA
Gate Operating Current	I _G	V _{DG} = 20 V, I _D = 200 μA		-5	-50	pA
		T _A = 125 °C		-0.8	-250	nA
Gate-Source Voltage	V _{GS}	V _{DG} = 20 V, I _D = 200 μA	-0.5	-1.5	-4	V
		I _D = 50 μA			-4.2	
Gate-Source Forward Voltage	V _{GS(F)}	I _G = 1 mA, V _{DS} = 0 V			2	
Dynamic						
Common-Source Forward Transconductance	g _{fs}	V _{DS} = 20 V, V _{GS} = 0 V f = 1 kHz	1	2.5	3	mS
Common-Source Output Conductance	g _{os}			2	35	μS
Common-Source Input Capacitance	C _{iss}	V _{DS} = 20 V, V _{GS} = 0 V f = 1 MHz		3	4	pF
Common-Source Reverse Transfer Capacitance	C _{rss}			1	1.2	
Drain-Gate Capacitance	C _{dg}	V _{DG} = 10 V, I _S = 0, f = 1 MHz			1.5	
Equivalent Input Noise Voltage	e _n	V _{DS} = 20 V, V _{GS} = 0 V, f = 1 kHz		9		nV/ √Hz
Noise Figure	NF	V _{DS} = 20 V, V _{GS} = 0 V f = 100 Hz, R _G = 10 MΩ			0.5	dB
Matching						
Differential Gate-Source Voltage	V _{GS1} - V _{GS2}	V _{DG} = 20 V, I _D = 200 μA		15	25	mV
Gate-Source Voltage Differential Change with Temperature	$\frac{\Delta V_{GS1} - V_{GS2} }{\Delta T}$	V _{DG} = 20 V, I _D = 200 μA T _A = -55 to 125 °C		20	100	μV/°C
Saturation Drain Current Ratio	$\frac{I_{DSS1}}{I_{DSS2}}$	V _{DS} = 20 V, V _{GS} = 0 V	0.85	0.97	1	
Transconductance Ratio	$\frac{g_{fs1}}{g_{fs2}}$	V _{DS} = 20 V, I _D = 200 μA f = 1 kHz	0.85	0.97	1	
Differential Output Conductance	g _{os1} - g _{os2}				0.1	
Differential Gate Current	I _{G1} - I _{G2}	V _{DG} = 20 V, I _D = 200 μA T _A = 125 °C		0.1	10	nA
Common Mode Rejection Ratio ^c	CMRR	V _{DG} = 10 to 20 V, I _D = 200 μA		100		dB

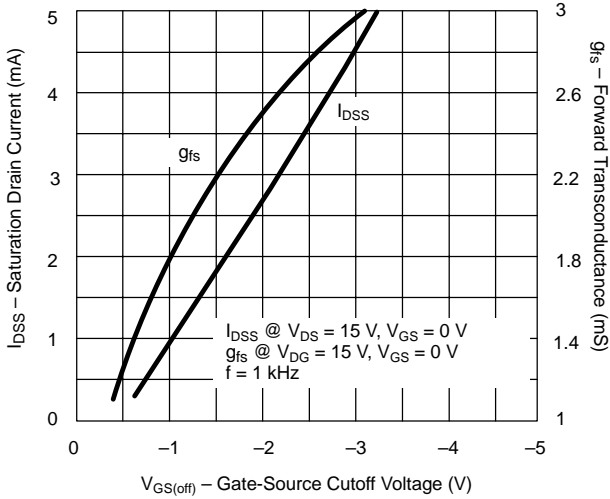
Notes

- a. Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing.
 b. Pulse test: PW ≤ 300 μs duty cycle ≤ 3%.
 c. This parameter not registered with JEDEC.

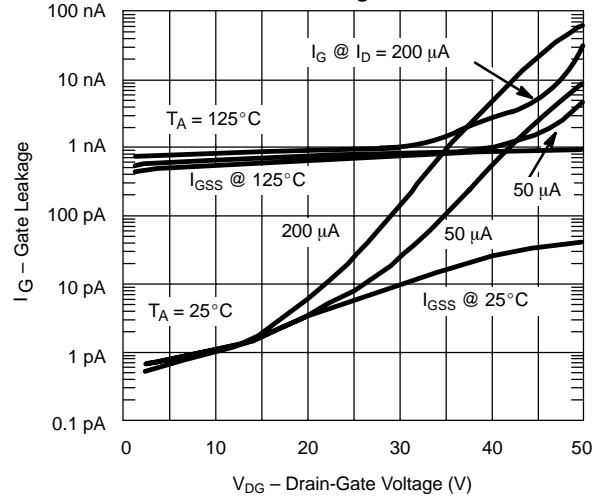
NQP

TYPICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)

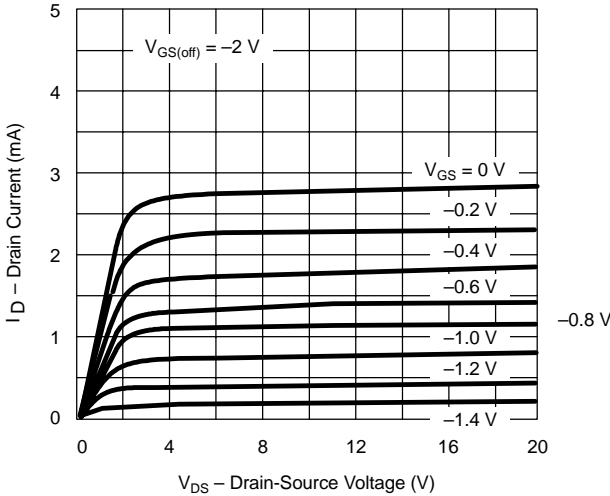
Drain Current and Transconductance vs. Gate-Source Cutoff Voltage



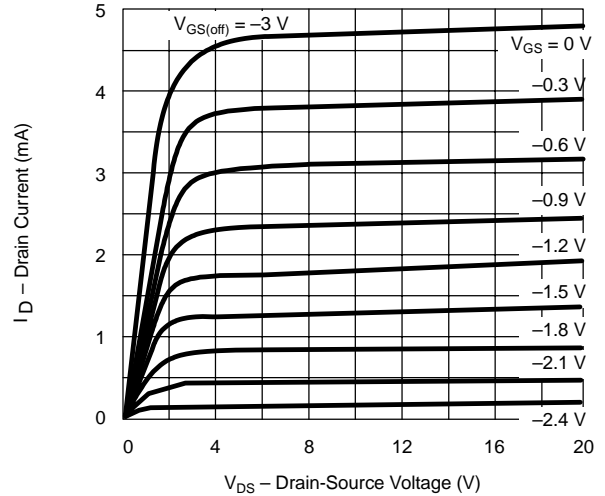
Gate Leakage Current



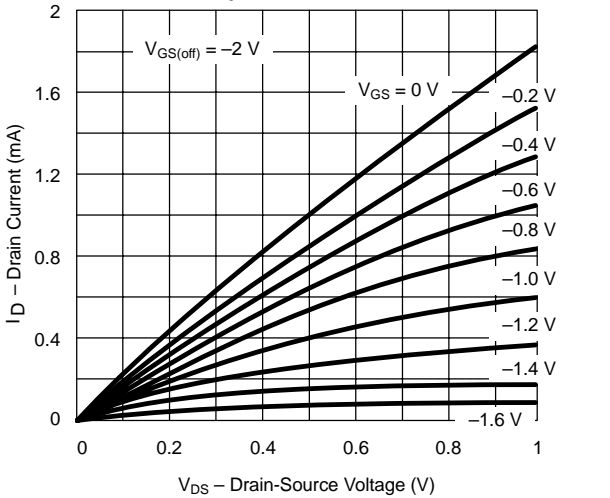
Output Characteristics



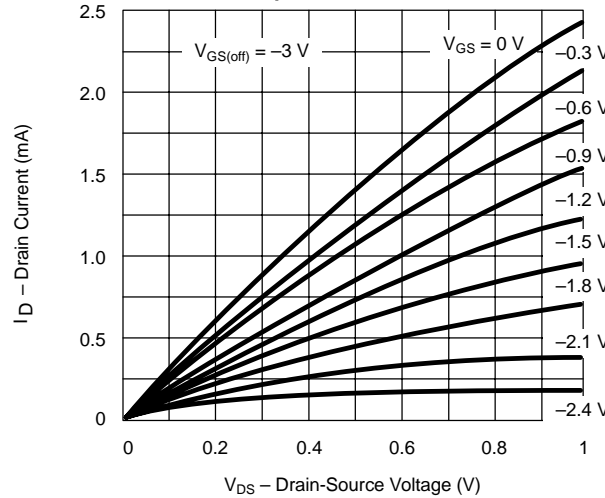
Output Characteristics



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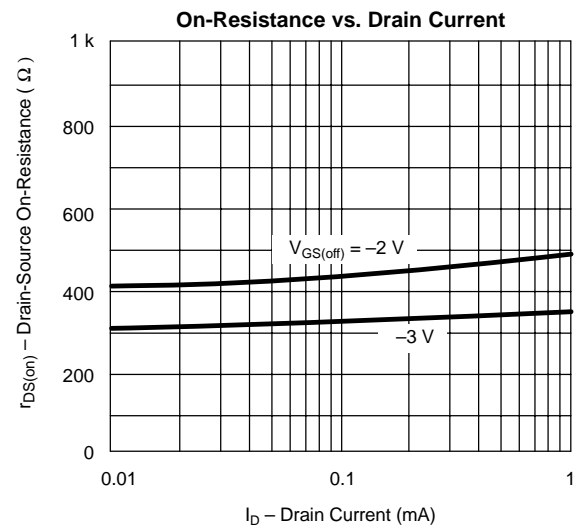
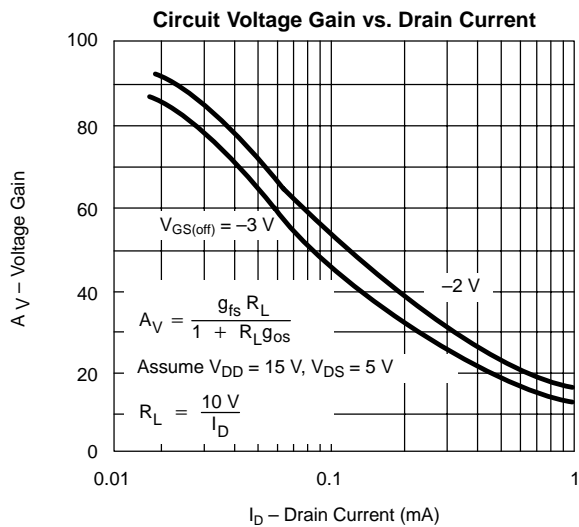
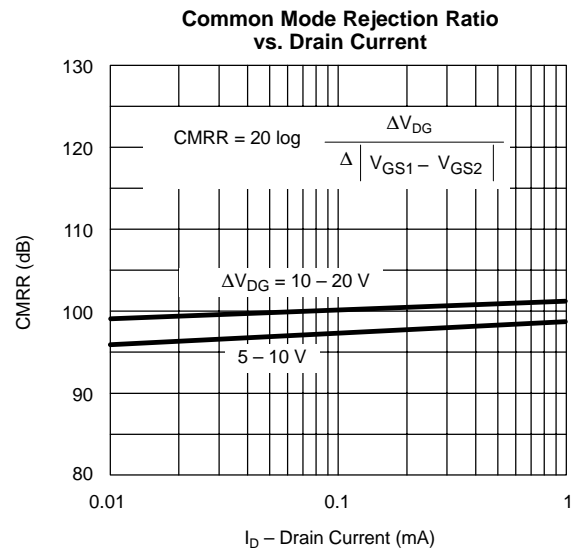
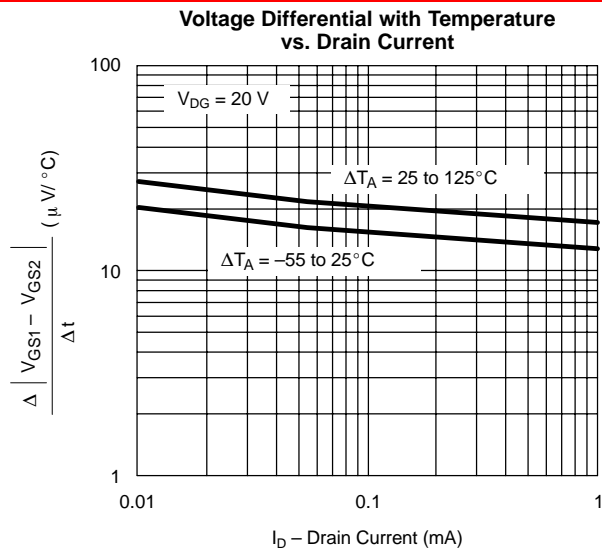
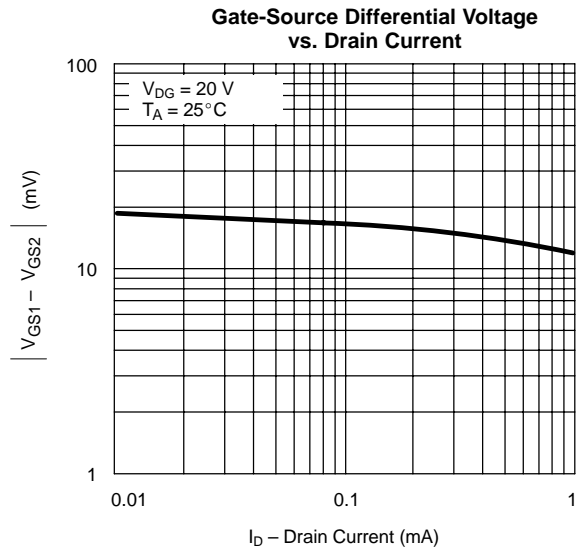
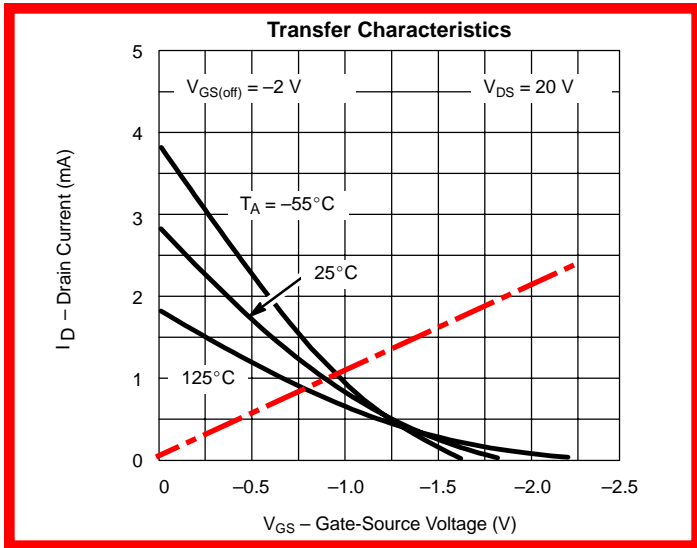


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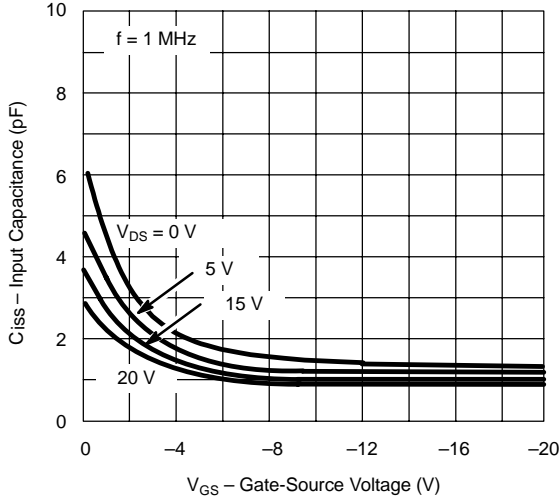
TYPICAL CHARACTERISTICS (T_A = 25°C UNLESS OTHERWISE NOTED)



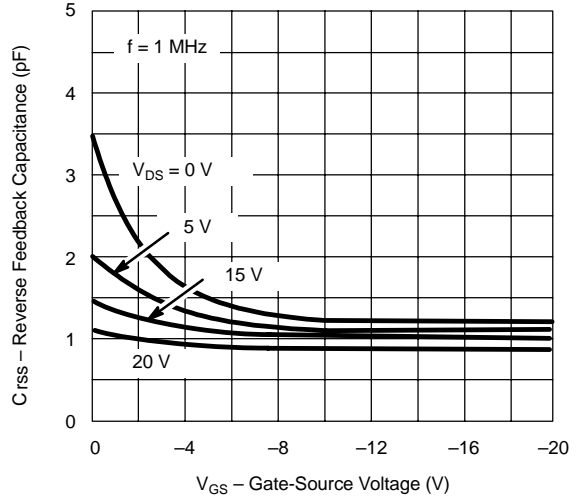


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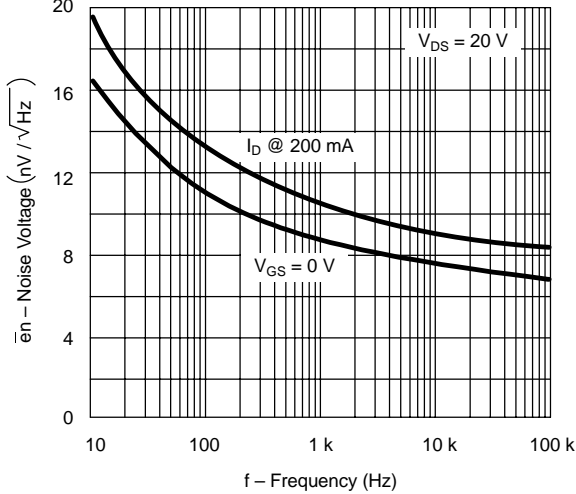
Common-Source Input Capacitance vs. Gate-Source Voltage



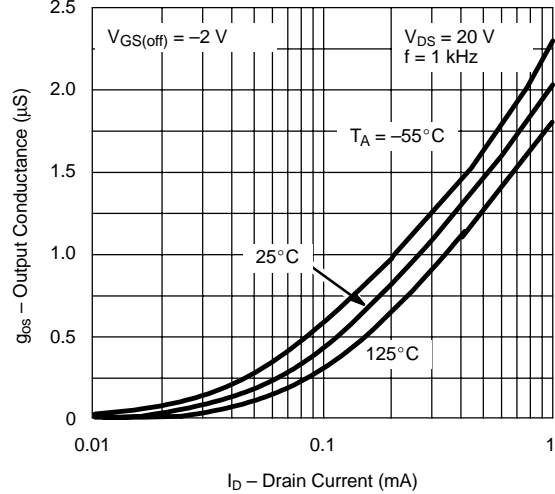
Common-Source Reverse Feedback Capacitance vs. Gate-Source Voltage



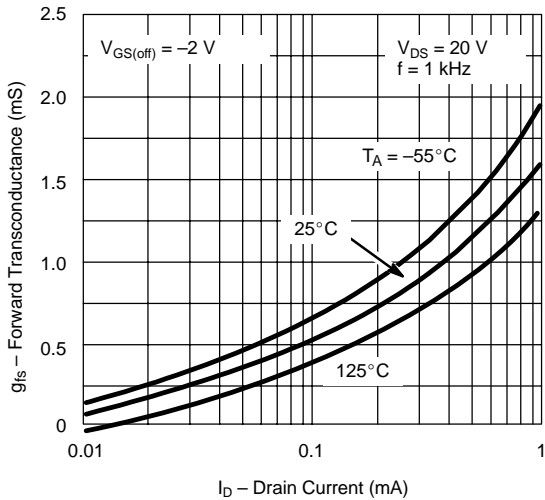
Equivalent Input Noise Voltage vs. Frequency



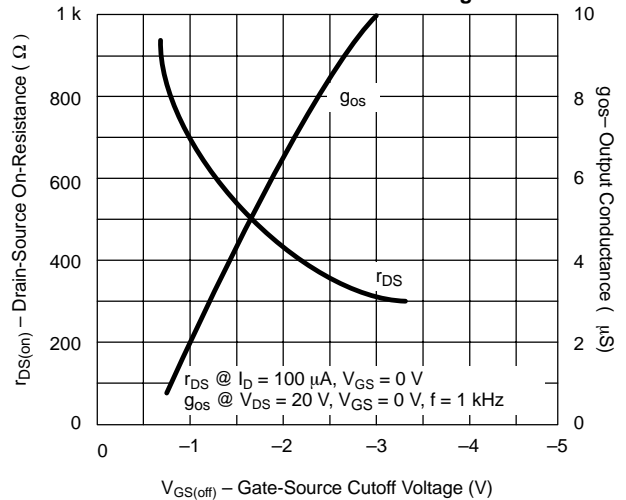
Output Conductance vs. Drain Current



Common-Source Forward Transconductance vs. Drain Current



On-Resistance and Output Conductance vs. Gate-Source Cutoff Voltage





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